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# 2SK1215

Silicon N-Channel MOS FET

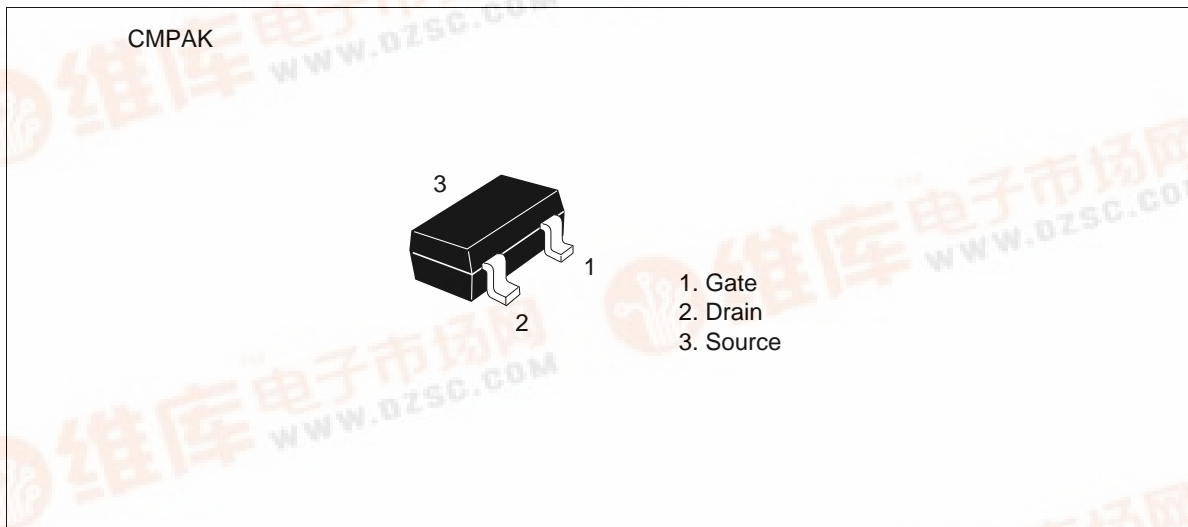
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## Application

VHF amplifier

## Outline



## 2SK1215

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSX}^{*1}$	20	V
Gate to source voltage	$V_{GSS}$	±5	V
Drain current	$I_D$	30	mA
Gate current	$I_G$	±1	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1.  $V_{GS} = -4$  V

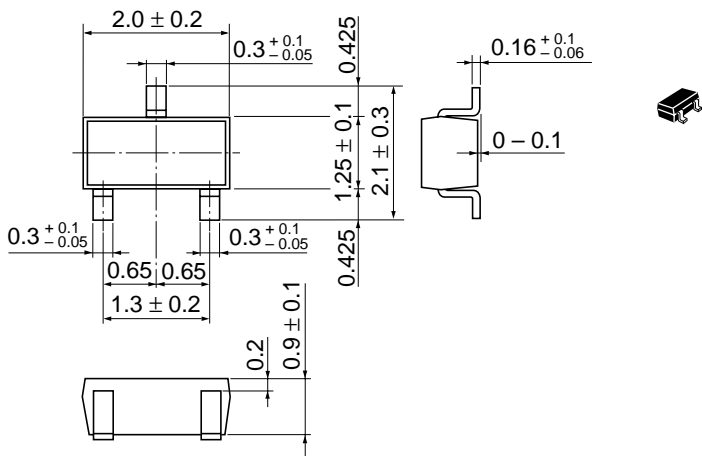
### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	20	—	—	V	$I_D = 100 \mu A, V_{GS} = -4$ V
Gate cutoff current	$I_{GSS}$	—	—	±20	nA	$V_{GS} = \pm 5$ V, $V_{DS} = 0$
Drain current	$I_{DSS}^{*1}$	4	—	12	mA	$V_{DS} = 10$ V, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0	—	-2.0	V	$V_{DS} = 10$ V, $I_D = 10 \mu A$
Forward transfer admittance	$ y_{fs} $	8	14	—	mS	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ kHz
Input capacitance	Ciss	—	2.5	—	pF	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ MHz
Output capacitance	Coss	—	1.6	—	pF	
Reverse transfer capacitance	Crss	—	0.03	—	pF	
Power gain	PG	24	—	—	dB	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 100$ MHz
Noise figure	NF	—	—	3	dB	

Note: 1. The 2SK1215 is grouped by  $I_{DSS}$  as follows.

Grade	D	E	F
Mark	IGD	IGE	IGF
$I_{DSS}$	4 to 8	6 to 10	8 to 12

See characteristic curves of 2SK359.



Unit: mm

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## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      NorthAmerica      : <http://semiconductor.hitachi.com/>  
             Europe                : <http://www.hitachi-eu.com/hel/ecg>  
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### For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher StraÙe 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00  
  
Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX